2SA2057

Silicon PNP epitaxial planar type

Power supply for audio & visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

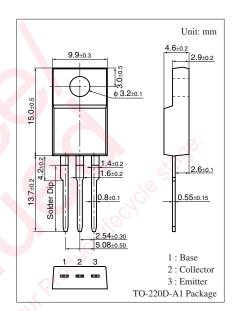
■ Features

- \bullet High speed switching (t_{stg} : storage time/ t_f : fall time is short)
- \bullet Low collector-emitter saturation voltage $V_{\text{CE}(\text{sat})}$
- Superior forward current transfer ratio h_{FE} linearity
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

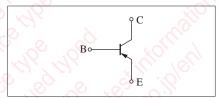
■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-60	V	
Emitter-base voltage (Collector open)	V_{EBO}	-6	V	
Collector current	I_{C}	-3	A	
Peak collector current *	I_{CP}	-6	A	
Collector power dissipation	P _C	20	W	
$T_a = 25$ °C		2.0		
Junction temperature	Tj	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	

Note) *: Non-repetitive peak collector current



Internal Connection



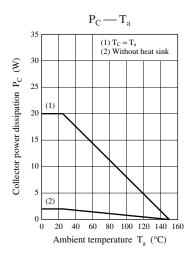
■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

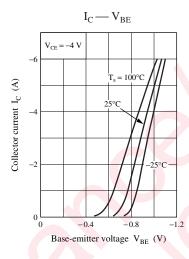
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -10 \text{ mA}, I_B = 0$	-60			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -60 \text{ V}, I_E = 0$			-100	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -60 \text{ V}, I_{B} = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-1	mA
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -4 \text{ V}, \ I_{C} = -1 \text{ A}$	120		320	_
	h _{FE2}	$V_{CE} = -4 \text{ V}, \ I_{C} = -3 \text{ A}$	40			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -3 \text{ A}, I_B = -0.375 \text{ A}$			- 0.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -0.1 \text{ A}, f = 10 \text{ MHz}$		90		MHz
Turn-on time	t _{on}	$I_C = -1$ A, Resistance loaded		0.15	0.30	μs
Storage time	t _{stg}	$I_{B1} = -0.1 \text{ A}, I_{B2} = 0.1 \text{ A}$		0.4	0.7	μs
Fall time	t _f	$V_{CC} = 50 \text{ V}$		0.10	0.15	μs

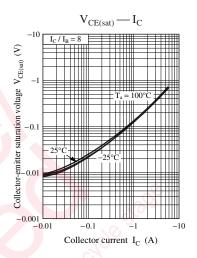
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

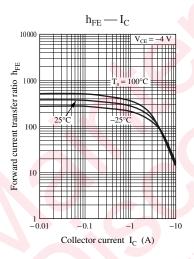
2. *: Rank classification

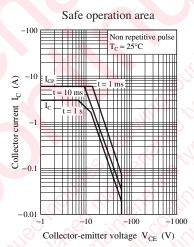
Rank	Q	Р
h_{FE1}	120 to 250	160 to 320

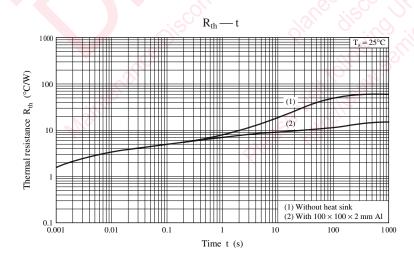












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